AMENDMENTS TO THE CLAIMS:

1-4. (Canceled)

5. (Currently amended) A method of manufacturing a DRAM-incorporated semiconductor device in which a DRAM section and a logic section are formed on a semiconductor substrate that is isolated into elements, said method comprising:

forming a metal film comprising one of cobalt and nickel directly on surfaces of highly doped source-drain regions and gate regions in said DRAM section and said logic section; and

heat treating said device to react said metal film with said surfaces to concurrently form a metal silicide layer in each of said DRAM section and said logic section.

6. (Currently amended) The method of manufacturing a semiconductor device according to Claim 5, wherein said metal film is formed over an entire surface of said substrate, and wherein said heat treating comprises:

heating said device at 500-600°C;

removing unreacted metal film with a mixed solution of sulfuric acid and hydrogen peroxide; and

heating said device at 800°C ~~removes unreacted metal film~~.

7. (Currently amended) The method of manufacturing a semiconductor device according to Claim 6, wherein said metal film comprises ~~is selected from the group consisting of titanium,~~ cobalt ~~and nickel~~.

8. (Original) The method of manufacturing a semiconductor device according to Claim 5, wherein dopant implantation into gates are carried out concurrently with formation of the source-drain regions that constitute transistors in the DRAM section and the logic section, and thereby P-N gates are formed.

9. (Previously presented) The method of manufacturing a semiconductor device

according to Claim 5, further comprising:

forming a bit contact connecting said DRAM section with a bit line and a contact plug connecting to said source-drain in said logic section, said bit contact and said contact plug comprising a metal material.

10-11. (Canceled)

12. (Currently amended) A method of manufacturing a semiconductor device having a memory cell section and an adjacent circuit section, said method comprising:

forming a metal film comprising one of cobalt and nickel directly on surfaces of highly doped source-drain regions and gate regions in said memory cell section and said adjacent circuit section; and

annealing said device to react said metal film with said surfaces to concurrently form a metal silicide layer in each of said memory cell section and said adjacent circuit section.

13. (Currently amended) The method of manufacturing a semiconductor device according to Claim 12, wherein said forming a metal film comprises forming a metal film over an entire surface of said substrate, and wherein said heat treating comprises:

heating said device at 500-600°C;

removing unreacted metal film with a mixed solution of sulfuric acid and hydrogen peroxide; and

heating said device at 800°C ~~removes unreacted metal film~~.

14. (Currently amended) The method of manufacturing a semiconductor device according to Claim 13, wherein said metal film comprises ~~is selected from the group consisting of titanium;~~ cobalt ~~and nickel~~.

15. (Currently amended) A method of manufacturing a semiconductor device comprising:

forming a metal film comprising one of cobalt and nickel on source-drain and gate surfaces in a memory cell section of a substrate, and on source-drain and gate surfaces in an adjacent circuit section of said substrate; and

heat treating said device to react said metal film with silicon in said surfaces to concurrently form a metal silicide layer in each of said memory cell section and said adjacent circuit section.

16. (Previously presented) The method of manufacturing a semiconductor device according to Claim 12, wherein said forming a metal film comprises a sputtering method.

17. (Currently amended) The method of manufacturing a semiconductor device according to Claim 12, wherein said heat treating comprises:

heating said device at 500-600°C in a nitrogen atmosphere for 30 seconds; ; and

heating said device at 800 °C in a nitrogen atmosphere for 10 seconds.

18. (Currently amended) The method of manufacturing a semiconductor device according to Claim 12, wherein said metal film comprises nickel ~~source-drain regions in said memory cell section comprise a high dopant concentration~~.

19. (Previously presented) The method of manufacturing a semiconductor device according to Claim 12, further comprising:

forming an ohmic contact on said silicide layer on a source-drain region.

20. (Previously presented) The method of manufacturing a semiconductor device according to Claim 12, further comprising:

forming source-drain regions in said memory cell section and said adjacent circuit section.

21. (Currently amended) The method of manufacturing a semiconductor device according to Claim 20, wherein said forming source-drain regions comprises implanting BF_2 ions in a source-drain region at an accelerating voltage of 20 keV and a dose of 3×10^{15} atoms/cm^2 ~~a concentration of 3×10^{17}/ cm^3~~.

22. (Currently amended) The method of manufacturing a semiconductor device according

to Claim 20, wherein said forming source-drain regions comprises implanting Arsenic ~~Arsenic~~ ions in a source-drain region at an accelerating voltage of 50 keV and a dose in a range of 3×10^{15} to 6×10^{15} atoms/cm^2 ~~a concentration of 6×10^{15}/cm^3~~.